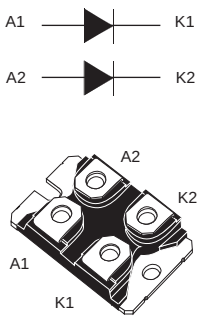
STTH200F04

Ultrafast high voltage rectifier

Datasheet - production data



ISOTOP

Description

This device, which uses ST 400 V technology, is especially suited for use in switching welding equipment.

Table 1: Device summary

Symbol	Value
$I_{F(AV)}$	2 x 100 A
V_{RRM}	400 V
T_j (max.)	150 °C
V_F (typ.)	0.95 V
t_{rr} (max.)	70 ns

Features

- Ultrafast switching
- Low reverse current
- Low thermal resistance
- Reduces switching and conduction losses
- Insulated package ISOTOP:
  - Insulated voltage: 2500 V_{RMS} sine
  - Capacitance: 45 pF
- ECOPACK®2 compliant component

TM: ISOTOP is a trademark of STMicroelectronics

1 Characteristics

Table 2: Absolute ratings (limiting values, per diode)

Symbol	Parameter		Value	Unit
V_{RRM}	Repetitive peak reverse voltage		400	V
$I_{F(RMS)}$	Forward rms current		200	A
$I_{F(AV)}$	Average forward current, δ = 0.5	T_C = 60 °C, per diode	100	A
I_{FSM}	Surge non repetitive forward current	t_p = 10 ms sinusoidal	1000	A
T_{stg}	Storage temperature range		-55 to +150	°C
T_j	Maximum operating junction temperature		150	°C

Table 3: Thermal parameters

Symbol	Parameter		Maximum values	Unit
$R_{th(j-c)}$	Junction to case	Per diode	0.60	°C/W
		Total	0.35	
$R_{th(c)}$	Coupling		0.1	

When the diodes 1 and 2 are used simultaneously:

ΔT_j (diode1) = $P_{(diode1)}$ x $R_{th(j-c)\ (per\ diode)}$ + $P_{(diode2)}$ x $R_{th(c)}$

Table 4: Static electrical characteristics (per diode)

Symbol	Parameter	Test conditions		Min.	Typ.	Max.	Unit
I_R (1)	Reverse leakage current	T_j = 25 °C	$V_R = V_{RRM}$	-		75	µA
		T_j = 125 °C		-	75	750	
V_F (2)	Forward voltage drop	T_j = 25 °C	I_F = 100 A	-		1.45	V
		T_j = 125 °C			0.95	1.20	
		T_j = 150 °C		-	0.90	1.15	
		T_j = 125 °C	I_F = 200 A	-	1.20	1.50	
		T_j = 150 °C		-	1.15	1.45	

Notes:

(1)Pulse test: t_p = 5 ms, δ < 2%

(2)Pulse test: t_p = 380 µs, δ < 2%

To evaluate the maximum conduction losses, use the following equation:

$P = 0.85 \times I_{F(AV)} + 0.003 \times I_F{}^2{}_{(RMS)}$

Table 5: Dynamic characteristics (per diode)

Symbol	Parameter	Test conditions		Min.	Typ.	Max.	Unit
t_{rr}	Reverse recovery time	T_j = 25 °C	I_F = 0.5 A, I_{rr} = 0.25 A, I_R = 1 A	-		80	ns
			I_F = 1 A, dI_F/dt = -50 A/µs, V_R = 30 V		70	95	
		T_j = 125 °C	I_F = 100 A, dI_F/dt = -200 A/µs, V_R = 50 V	-	105	140	
I_{RM}	Reverse recovery current	T_j = 125 °C	I_F = 100 A, dI_F/dt = -200 A/µs, V_R = 400 A/µs	-	15	20	A
Q_{RR}	Reverse recovery charge			-	750		nC
S	Softness factor			-	0.3		
t_{fr}	Forward recovery time	T_j = 25 °C	I_F = 100 A, dI_F/dt = 200 A/µs V_{FR} = 1.5 x V_{Fmax}	-	500	800	ns
V_{FP}	Forward recovery voltage	T_j = 25 °C	I_F = 100 A, dI_F/dt = 200 A/µs	-	2.9		V

1.1 Characteristics (curves)

Figure 1: Conduction losses versus average forward current (per diode)

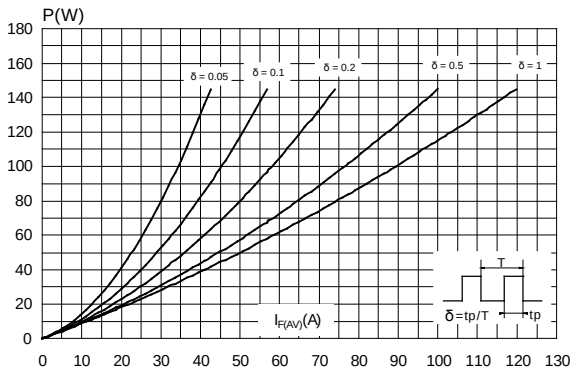


Figure 2: Forward voltage drop versus forward current (per diode)

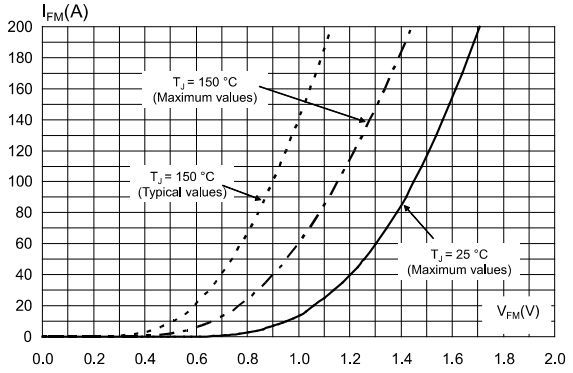


Figure 3: Relative variation of thermal impedance junction to case versus pulse duration

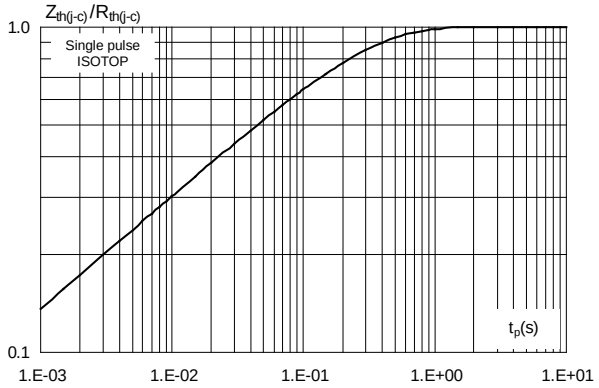


Figure 4: Peak reverse recovery current versus dI_F/dt (typical values, per diode)

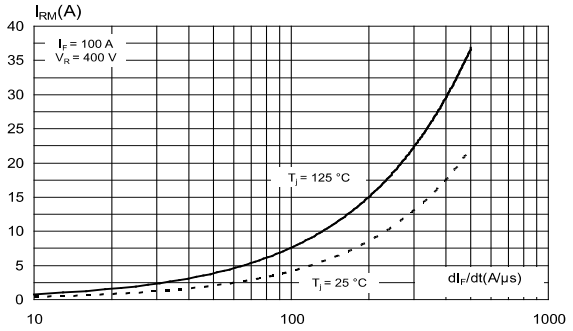


Figure 5: Reverse recovery time versus dI_F/dt (typical values, per diode)

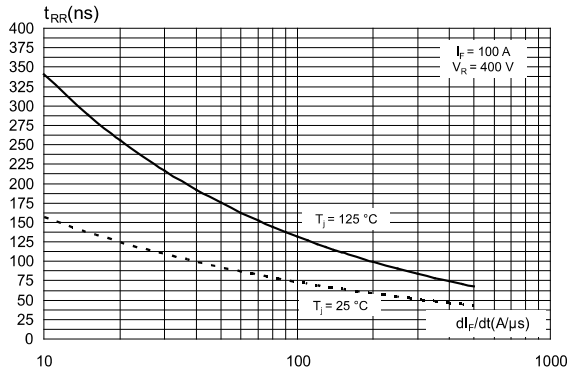


Figure 6: Reverse recovery charges versus dI_F/dt (typical values, per diode)

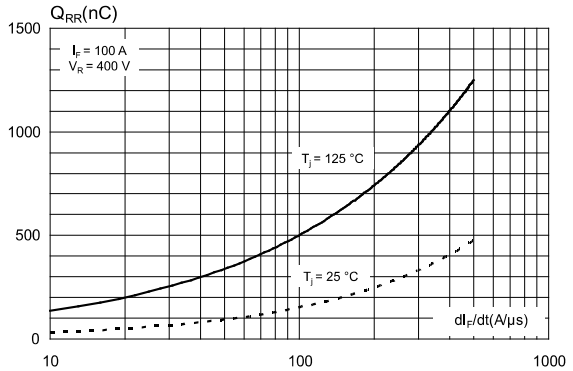


Figure 7: Relative variations of dynamic parameters versus junction temperature

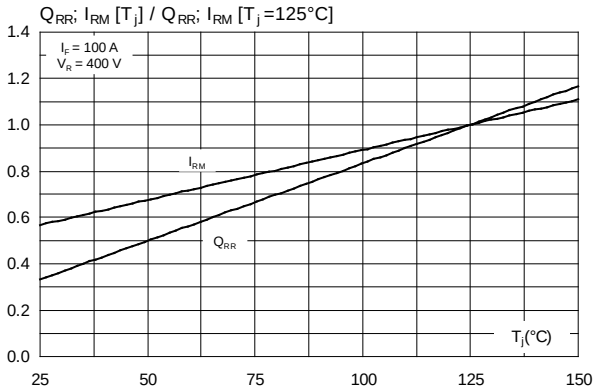


Figure 8: Transient peak forward voltage versus dI_F/dt (typical values, per diode)

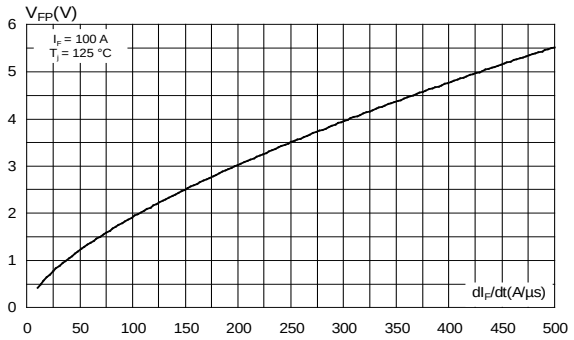


Figure 9: Forward recovery time versus dI_F/dt (typical values, per diode)

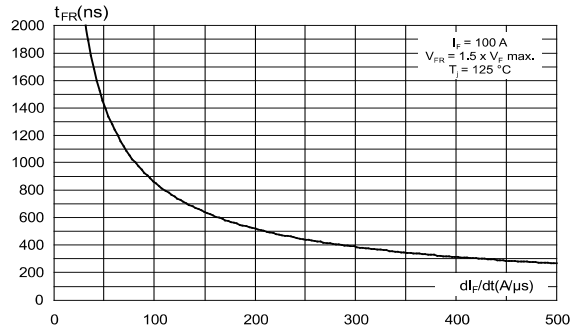
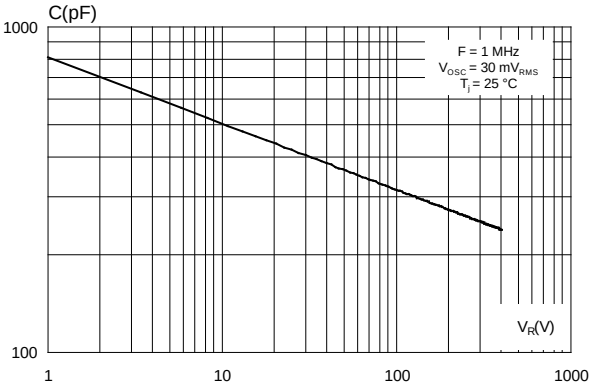


Figure 10: Junction capacitance versus reverse voltage applied (typical values, per diode)



2 Package information

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK® packages, depending on their level of environmental compliance. ECOPACK® specifications, grade definitions and product status are available at: ***www.st.com***. ECOPACK® is an ST trademark.

- Epoxy meets UL94, V0
- Cooling method: by conduction (C)
- Recommended torque value: 1.3 N·m
- Maximum torque value: 1.5 N·m

STMicroelectronics strongly recommends the use of the screws delivered with this product.

The use of any other screws is entirely at the user's own risk and will invalidate the warranty.

2.1 ISOTOP package information

Figure 11: ISOTOP package outline

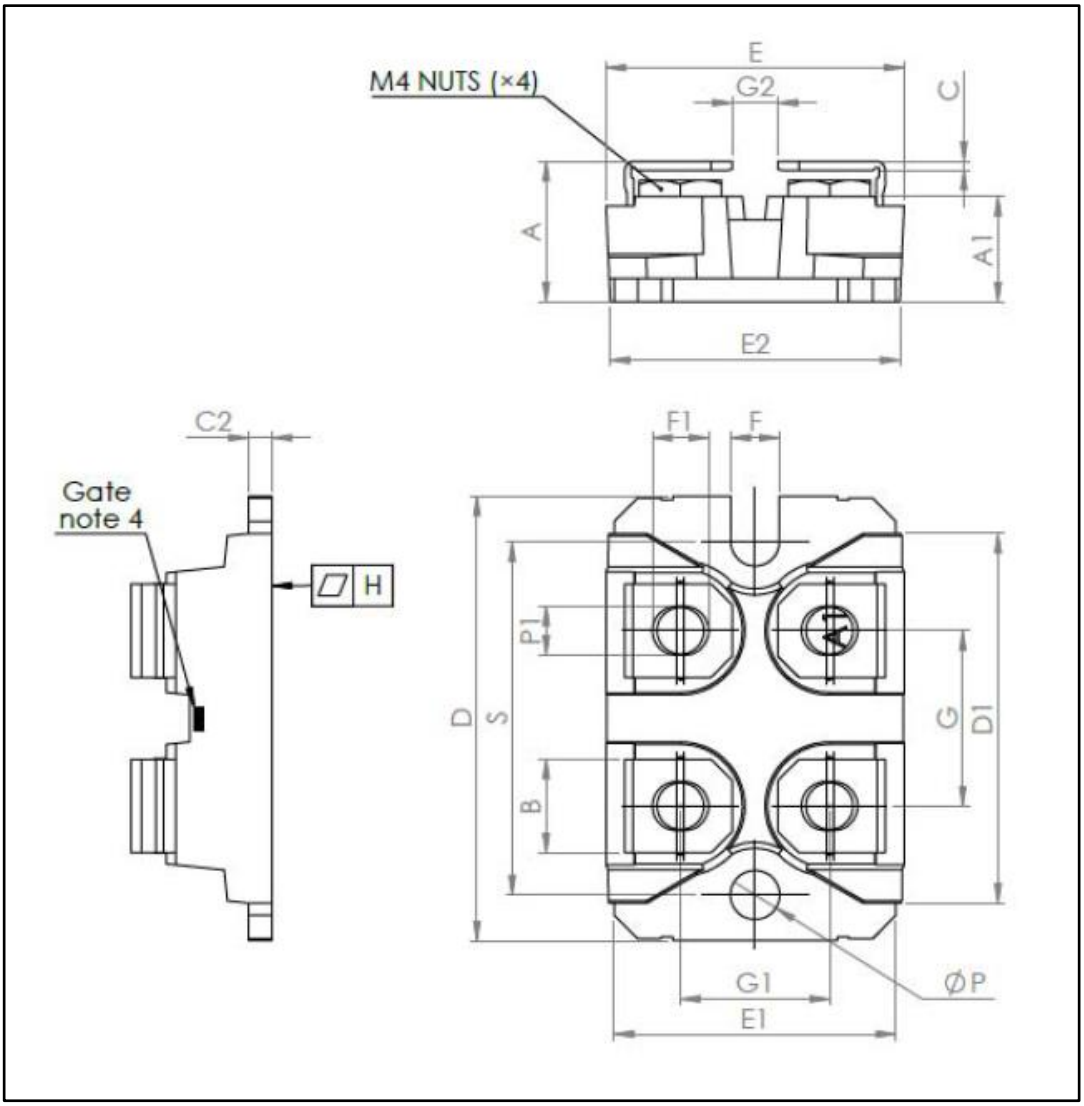


Table 6: ISOTOP package mechanical data

Ref.	Dimensions			
	Millimeters		Inches	
	Min.	Max.	Min.	Max.
A	11.80	12.20	0.460	0.480
A1	8.90	9.10	0.350	0.358
B	7.80	8.20	0.307	0.323
C	0.75	0.85	0.030	0.033
C2	1.95	2.05	0.077	0.081
D	37.80	38.20	1.488	1.504
D1	31.50	31.70	1.240	1.248
E	25.15	25.50	0.990	1.004
E1	23.85	24.15	0.939	0.951
E2	24.80		0.976	
G	14.90	15.10	0.587	0.594
G1	12.60	12.80	0.496	0.504
G2	3.50	4.30	0.138	0.169
F	4.10	4.30	0.161	0.169
F1	4.60	5	0.181	0.197
H	-0.05	0.1	-0.002	0.004
Diam P	4	4.30	0.157	0.169
P1	4	4.40	0.157	0.173
S	30.10	30.30	1.185	1.193

3 Ordering information

Table 7: Ordering information

Order code	Marking	Package	Weight	Base qty.(1)	Delivery mode
STTH200F04TV1	STTH200F04TV1	ISOTOP	27 g (without screws)	10 (with screws)	Tube

Notes:

(1)This product is supplied with 40 terminal screws and washers for each tube. The screws and washers are supplied in a separate pack with the order.

4 Revision history

Table 8: Document revision history

Date	Revision	Changes
04-Dec-2017	1	Initial release.

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